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Kind regards,

Team Nexperia



# PMEG4020EPA

# 2 A low V<sub>F</sub> MEGA Schottky barrier rectifier Rev. 01 — 16 December 2009

**Product data sheet** 

#### 1. **Product profile**

#### 1.1 General description

Planar Maximum Efficiency General Application (MEGA) Schottky barrier rectifier with an integrated guard ring for stress protection. PMEG4020EPA is encapsulated in an ultra thin SOT1061 leadless small Surface-Mounted Device (SMD) plastic package with medium power capability.

#### 1.2 Features

- Average forward current: I<sub>F(AV)</sub> ≤ 2 A
- Reverse voltage: V<sub>R</sub> ≤ 40 V
- Low forward voltage
- Exposed heat sink (cathode pad) for excellent thermal and electrical conductivity
- Leadless small SMD plastic package with medium power capability
- AEC-Q101 qualified

### 1.3 Applications

- Low voltage rectification
- High efficiency DC-to-DC conversion
- Switch Mode Power Supply (SMPS)
- Reverse polarity protection
- Low power consumption applications
- Battery chargers for mobile equipment

#### 1.4 Quick reference data

Quick reference data  $T_i = 25 \, ^{\circ}\text{C}$  unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$I_{F(AV)}$	average forward current	square wave; $\delta = 0.5$ ; $f = 20 \text{ kHz}$				
		$T_{amb} \le 65  ^{\circ}C$	[1] -	-	2	Α
		$T_{sp} \le 140  ^{\circ}C$	-	-	2	Α
$V_R$	reverse voltage		-	-	40	V
$V_{F}$	forward voltage	I <sub>F</sub> = 2 A	-	470	535	mV
$I_R$	reverse current	$V_R = 40 V$	-	20	100	μΑ

<sup>[1]</sup> Device mounted on a ceramic Printed-Circuit Board (PCB), Al<sub>2</sub>O<sub>3</sub>, standard footprint.



### 2. Pinning information

Table 2. Pinning

Pin	Description	Simplified outline	Graphic symbol
1	anode		54
2	anode	3	3
3	cathode	Transparent top view	006aab624

## 3. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
PMEG4020EPA	HUSON3	plastic thermal enhanced ultra thin small outline package; no leads; three terminals; body 2 $\times$ 2 $\times$ 0.65 mm	SOT1061		

### 4. Marking

Table 4. Marking codes

Type number	Marking code
PMEG4020EPA	A3

# 5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_R$	reverse voltage	T <sub>j</sub> = 25 °C	-	40	V
I <sub>F(AV)</sub>	average forward current	square wave; $\delta = 0.5$ ; $f = 20 \text{ kHz}$			
		$T_{amb} \le 65  ^{\circ}C$	<u>[1]</u> _	2	Α
		T <sub>sp</sub> ≤ 140 °C	-	2	Α
I <sub>FRM</sub>	repetitive peak forward current	$\begin{array}{l} t_p \leq 1 \text{ ms;} \\ \delta \leq 0.25 \end{array}$	<u>[2]</u> _	7	Α
I <sub>FSM</sub>	non-repetitive peak forward current	square wave; t <sub>p</sub> = 8 ms	[2][3]	18	Α
P <sub>tot</sub>	total power dissipation	$T_{amb} \le 25  ^{\circ}C$	[4][5]	520	mW
			[4][6]	1050	mW
			[4][1]	1900	mW

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Table 5. Limiting values ...continued

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
Tj	junction temperature		-	150	°C
T <sub>amb</sub>	ambient temperature		<b>–55</b>	+150	°C
T <sub>stg</sub>	storage temperature		-65	+150	°C

- [1] Device mounted on a ceramic PCB, Al<sub>2</sub>O<sub>3</sub>, standard footprint.
- [2] Both anode pins connected.
- [3]  $T_i = 25$  °C prior to surge.
- [4] Reflow soldering is the only recommended soldering method.
- [5] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [6] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm<sup>2</sup>.

### 6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-a)}$ thermal resistance from junction to ambient		in free air	[1][2]			
		[3] _	-	240	K/W	
			<u>[4]</u> _	-	120	K/W
			<u>[5]</u> _	-	65	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point		<u>[6]</u> _	-	10	K/W

- [1] For Schottky barrier diodes thermal runaway has to be considered, as in some applications the reverse power losses P<sub>R</sub> are a significant part of the total power losses.
- [2] Reflow soldering is the only recommended soldering method.
- [3] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [4] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm<sup>2</sup>.
- [5] Device mounted on a ceramic PCB, Al<sub>2</sub>O<sub>3</sub>, standard footprint.
- [6] Soldering point of cathode tab.

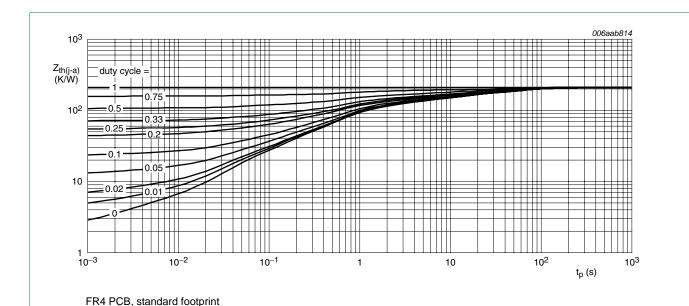


Fig 1. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

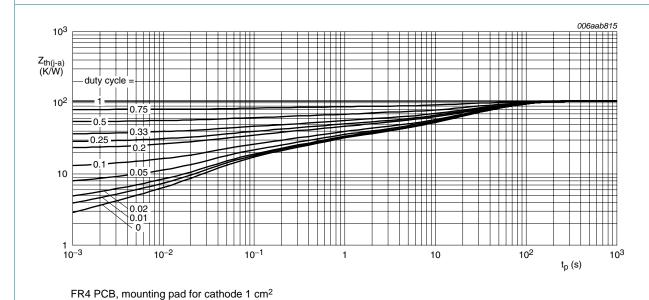
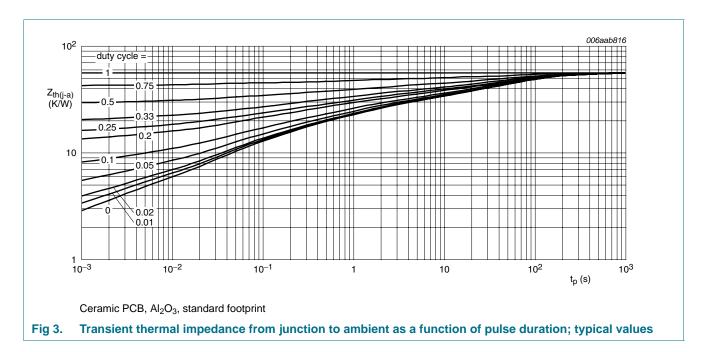


Fig 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



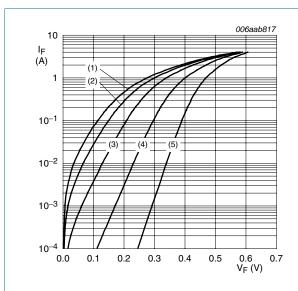
### 7. Characteristics

Table 7. Characteristics

 $T_i = 25$  °C unless otherwise specified.

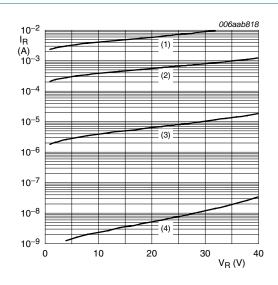
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{F}$	forward voltage	$I_F = 0.5 A$	-	360	-	mV
	I <sub>F</sub> = 1 A	-	400	-	mV	
		I <sub>F</sub> = 2 A	-	470	535	mV
I <sub>R</sub>	reverse current	V <sub>R</sub> = 10 V	-	5	-	μΑ
	V <sub>R</sub> = 40 V	-	20	100	μΑ	
C <sub>d</sub> diode capacitance	f = 1 MHz					
		V <sub>R</sub> = 1 V	-	270	-	pF
		V <sub>R</sub> = 10 V	-	100	-	pF
t <sub>rr</sub>	reverse recovery time		<u>[1]</u> -	85	-	ns

<sup>[1]</sup> When switched from  $I_F$  = 10 mA to  $I_R$  = 10 mA;  $R_L$  = 100  $\Omega$ ; measured at  $I_R$  = 1 mA.



- (1)  $T_j = 150 \, ^{\circ}C$
- (2)  $T_i = 125 \, ^{\circ}C$
- (3)  $T_j = 85 \,^{\circ}C$
- (4)  $T_i = 25 \,^{\circ}\text{C}$
- (5)  $T_i = -40 \, ^{\circ}\text{C}$

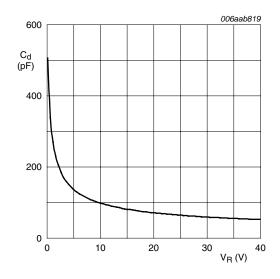
Fig 4. Forward current as a function of forward voltage; typical values



- (1)  $T_j = 125 \, ^{\circ}C$
- (2)  $T_j = 85 \, ^{\circ}C$
- (3)  $T_j = 25 \, ^{\circ}C$
- (4)  $T_j = -40 \, ^{\circ}C$

Fig 5. Reverse current as a function of reverse voltage; typical values

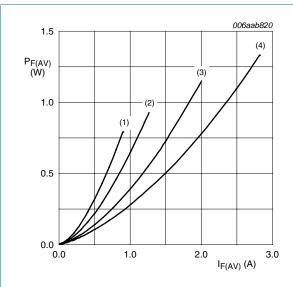
6 of 13



 $f = 1 \text{ MHz}; T_{amb} = 25 \text{ }^{\circ}\text{C}$ 

**Product data sheet** 

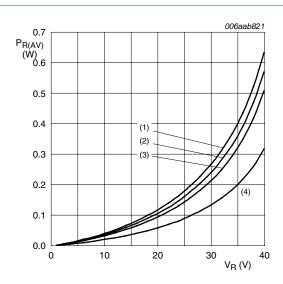
Fig 6. Diode capacitance as a function of reverse voltage; typical values



T<sub>j</sub> = 150 °C

- (1)  $\delta = 0.1$
- (2)  $\delta = 0.2$
- (3)  $\delta = 0.5$
- (4)  $\delta = 1$

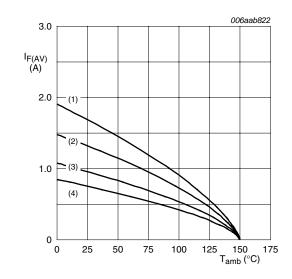
Fig 7. Average forward power dissipation as a function of average forward current; typical values



T<sub>i</sub> = 125 °C

- (1)  $\delta = 1$
- (2)  $\delta = 0.9$
- (3)  $\delta = 0.8$
- (4)  $\delta = 0.5$

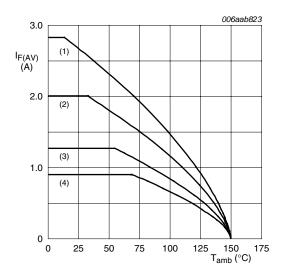
Fig 8. Average reverse power dissipation as a function of reverse voltage; typical values



FR4 PCB, standard footprint

- (1)  $\delta = 1$ ; DC
- (2)  $\delta = 0.5$ ; f = 20 kHz
- (3)  $\delta = 0.2$ ; f = 20 kHz
- (4)  $\delta = 0.1$ ; f = 20 kHz

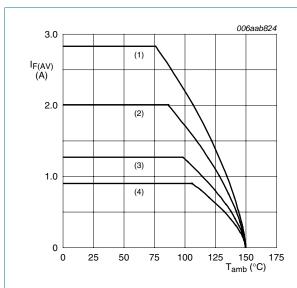
Fig 9. Average forward current as a function of ambient temperature; typical values



FR4 PCB, mounting pad for cathode 1 cm<sup>2</sup>

- (1)  $\delta = 1$ ; DC
- (2)  $\delta = 0.5$ ; f = 20 kHz
- (3)  $\delta = 0.2$ ; f = 20 kHz
- (4)  $\delta = 0.1$ ; f = 20 kHz

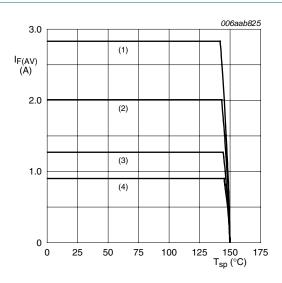
Fig 10. Average forward current as a function of ambient temperature; typical values



Ceramic PCB, Al<sub>2</sub>O<sub>3</sub>, standard footprint

- (1)  $\delta = 1$ ; DC
- (2)  $\delta = 0.5$ ; f = 20 kHz
- (3)  $\delta = 0.2$ ; f = 20 kHz
- (4)  $\delta = 0.1$ ; f = 20 kHz

Fig 11. Average forward current as a function of ambient temperature; typical values

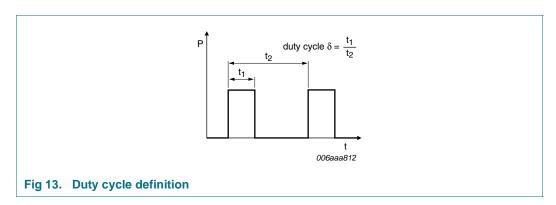


$$T_j = 150 \, ^{\circ}C$$

- (1)  $\delta = 1$ ; DC
- (2)  $\delta = 0.5$ ; f = 20 kHz
- (3)  $\delta = 0.2$ ; f = 20 kHz
- (4)  $\delta = 0.1$ ; f = 20 kHz

Fig 12. Average forward current as a function of solder point temperature; typical values

### 8. Test information



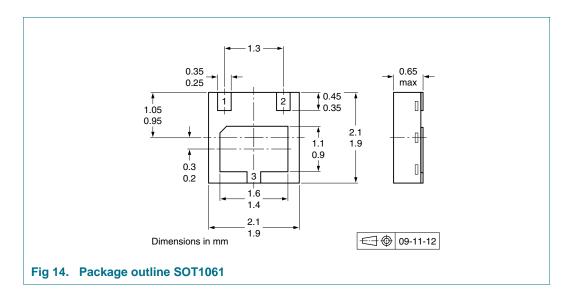
The current ratings for the typical waveforms as shown in Figure 9, 10, 11 and 12 are calculated according to the equations:  $I_{F(AV)} = I_M \times \delta$  with  $I_M$  defined as peak current,

 $I_{RMS}=I_{F(AV)}$  at DC, and  $I_{RMS}=I_{M} imes\sqrt{\delta}$  with  $I_{RMS}$  defined as RMS current.

### 8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

### 9. Package outline



### 10. Packing information

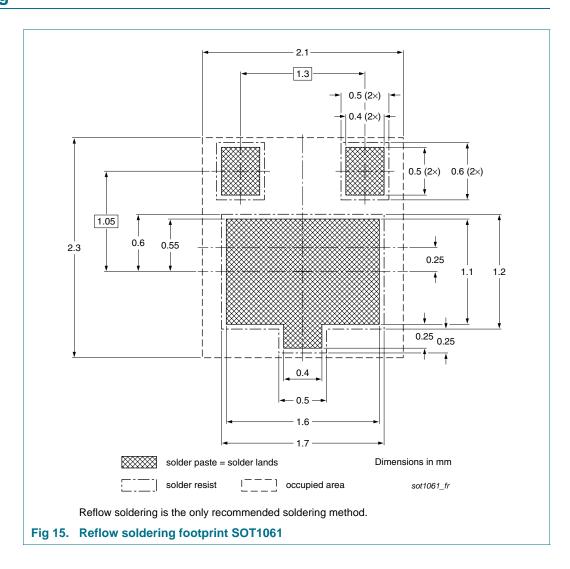
Table 8. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number	Package	Description	Packing quantity
			3000
PMEG4020EPA	SOT1061	4 mm pitch, 8 mm tape and reel	-115

<sup>[1]</sup> For further information and the availability of packing methods, see Section 14.

### 11. Soldering





### 12. Revision history

### Table 9. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PMEG4020EPA_1	20091216	Product data sheet	-	-

### 13. Legal information

#### 13.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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# PMEG4020EPA

### 2 A low V<sub>F</sub> MEGA Schottky barrier rectifier

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